# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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### Contact us

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Unit: mm

4.0±0.2

0.45+0

1: Emitter 2: Collector 3: Base EIAJ: SC-43A TO-92-B1 Package

5.0±0.2

## 2SC2631

### Silicon NPN epitaxial planar type

For low-frequency high breakdown voltage amplification Complementary to 2SA1123

#### Features

- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Small collector output capacitance (Common base, input open cir cuited) Cob

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

	- a		-	
Parameter	Symbol	Rating	Unit	0.45 <sup>+0.15</sup> 2.5 <sup>+0.6</sup> 2.5 <sup>+0.6</sup> 2.5 <sup>+0.6</sup>
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	150	V	2.5_0.2 2.5_0.2
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	150	v	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V	
Collector current	Ι <sub>C</sub>	50	mA	KOV G
Peak collector current	I <sub>CP</sub>	100	mA	<u> </u>
Collector power dissipation	P <sub>C</sub>	750	mW	NILLS CS. A
Junction temperature	Tj	150	°€O	
Storage temperature	T <sub>stg</sub>	-55 to +150	<u> 60</u>	ar al al
			6	

Peak collector current	I <sub>CP</sub>	100 mA	$\sim$
Collector power dissipation	P <sub>C</sub>	750 mW	and the
Junction temperature	Tj		<b>)</b> ``
Storage temperature	T <sub>stg</sub> -	-55 to +150 400 0 40 40 40 40 40	
Electrical Characteristics T	,= 25°C	±3%des internance thed the latest	
Parameter	Symbol	Conditions Min Typ Max	Unit
Collector-emitter voltage (Base open)	VEEO	$L_{c} = 100 \mu A_{c} L_{B} = 0$ (150)	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = 10 \ \mu A, I_C \ge 0$	V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 100 V_{cH} = 0$ 1	μΑ
Forward current transfer ratio * G	h <sub>FE</sub>	$V_{CE} = 5V, I_C = 10 \text{ mA}$ 130 330	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 30 {\rm mA}, I_{\rm B} = 3 {\rm mA}$ 1	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$ 160	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 V, I_E = 0, f = 1 \text{ MHz}$ 3	pF
(Common base, input open circuited)		GIL NU	
Noise voltage	NV	$V_{CE} = 40$ V, $I_C = 1$ mA, $G_V = 80$ dB 150 300	mV
		$R_g \le 100 \text{ k}\Omega$ , Function = FLAT	

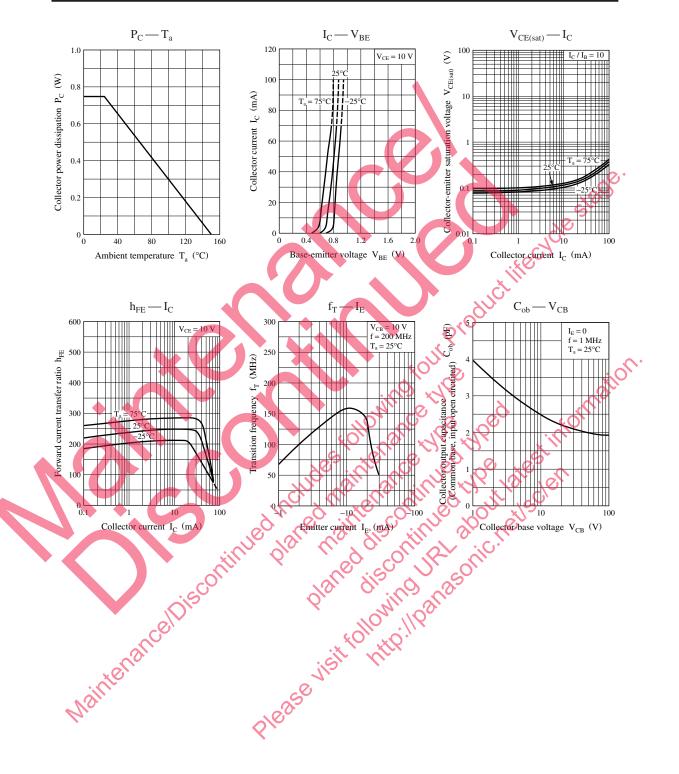
Note Measuring methods are based on JAPANESEINDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	R	s
h <sub>FE</sub>	130 to 220	185 to 330

#### 2SC2631





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